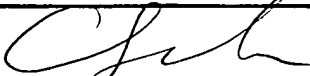


1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Complete If Known	
LIST OF PRIOR ART CITED BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/ 780, 929
				Filing Date	February 17, 2004
				First Named Inventor	DOUGLAS JAMES TWEET
				Group Art Unit	
				Examiner Name	
Sheet	1	of	2	Attorney Docket No.	SLA.0735

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number	Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
CAL		6,464,780	B1	Mantl et al.	10-15-02	
CAL		6,562,703	B1	Maa et al.	05-13-03	
CAL		2003/0143783	A1	Maa et al.	07-31-03	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T ²
		Office Code ³	Number ⁴	Kind				

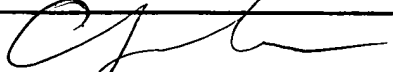
OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²

Examiner Signature		Date Considered	6/6/05
--------------------	---	-----------------	--------

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶Applicant is to place a check mark here if English language Translation is attached

1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Complete If Known	
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Application Number	10/780,929
				Filing Date	February 17, 2004
				First Named Inventor	DOUGLAS JAMES TWEET
				Group Art Unit	
				Examiner Name	
Sheet	2	of	2	Attorney Docket No.	SLA.0735

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.		T ²
CAI		RIM <i>et al.</i> , <i>Strained Silicon NMOSFETs for high performance CMOS technology</i> , 2001 Symposium on VLSI Technology Digest of Technical Papers, p. 59, IEEE (2001)		
		NAYAK <i>et al.</i> , <i>High-mobility Strained-Silicon PMOSFETs</i> , IEEE Transactions on Electron Devices, Vol. 43, 1709 (1996)		
		WELDON <i>et al.</i> , <i>On the mechanism of the hydrogen-induced exfoliation of silicon</i> , J. Vac. Sci. Technol. B. 15, 1065, (1997)		
		MANTL <i>et al.</i> , <i>Strain relaxation of epitaxial SiGe layers on Silicon(100) improved by hydrogen implantation</i> , Nuclear Instruments and Methods in Physics Research B 147, 29, (1999)		
		TRINKAUS <i>et al.</i> , <i>Strain relaxation mechanism for hydrogen-implanted Si_{1-x}Ge_x/Silicon(100) heterostructures</i> , Appl. Phys. Lett., 76, 3552, (2000)		
		CEROFOLINI, <i>et al.</i> , <i>Hydrogen-related complexes as the stressing species in high-fluence, hydrogen-implanted, single-crystal silicon</i> , Physical Review B, vol. 46, p. 2061 (1992)		
		FRABBONI <i>et al.</i> , <i>Static disorder depth profile in ion implanted materials by means of large angle convergent beam electron diffraction</i> , Physical Review Letters, vol. 81, 3155 (1998)		
CAI		FRABBONI, <i>Lattice strain and static disorder in hydrogen-implanted and annealed single-crystal silicon as determined by large-angle convergent-beam electron diffraction</i> , Physical Review B, vol. 65, 165436 (2002)		

Examiner Signature		Date Considered	6/6/05
--------------------	---	-----------------	--------

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
 *Unique citation designation number. *See attached Kinds of U.S. Patent Documents. *Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). *For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. *Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. *Applicant is to place a check mark here if English language Translation is attached